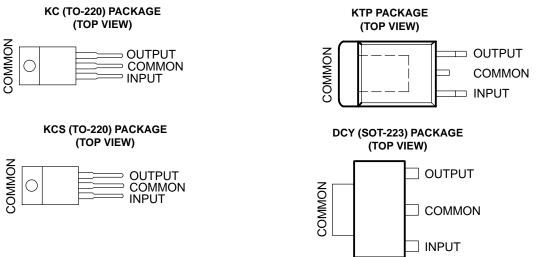
- 3-Terminal Regulators
- Output Current Up To 500 mA
- No External Components
- Internal Thermal-Overload Protection



- Internal Short-Circuit Current Limiting
- Output Transistor Safe-Area Compensation



description/ordering information

ORDERING INFORMATION

TJ	V _O (NOM) (V)	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
		Power Flex (KTP)	Reel of 3000	μΑ78M33CKTPR	UA78M33C
	3.3	SOT-223 (DCY)	Tube of 80	μΑ78M33CDCY	C3
3.3	3.3	301-223 (DC1)	Reel of 2500	μΑ78M33CDCYR	CS
		TO-220 (KC)	Tube of 50	μΑ78M33CKC	UA78M33C
		Power Flex (KTP)	Reel of 3000	μΑ78M05CKTPR	UA78M05C
5	SOT-223 (DCY)	Tube of 80	μΑ78M05CDCY	C5	
	5	301-223 (DC1)	Reel of 2500	μΑ78M05CDCYR	Co
		TO-220 (KC)	Tube of 50	μΑ78M05CKC	UA78M05C
0°C to 125°C		TO-220, short shoulder (KCS)	Tube of 20	μΑ78M05CKCS	UA76IVIUSC
	6	Power Flex (KTP)	Reel of 3000	μΑ78M06CKTPR	UA78M06C
		Power Flex (KTP)	Reel of 3000	μΑ78M08CKTPR	UA78M08C
	8	SOT-223 (DCY)	Tube of 80	μΑ78M08CDCY	C8
	0	301-223 (DC1)	Reel of 2500	μΑ78M08CDCYR	Co
		TO-220 (KC)	Tube of 50	μΑ78M08CKC	UA78M08C
	9	Power Flex (KTP)	Reel of 3000	μΑ78M09CKTPR	UA78M09C
	12	Power Flex (KTP)	Reel of 3000	μΑ78M12CKTPR	UA78M12C
	12	TO-220 (KC)	Tube of 50	μΑ78M12CKC	UA78M12C

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



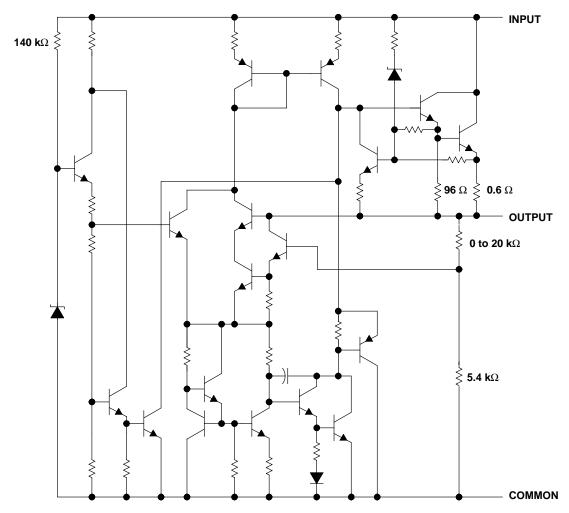
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



description/ordering information (continued)

This series of fixed-voltage integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 500 mA of output current. The internal current-limiting and thermal-shutdown features of these regulators essentially make them immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents, and also as the power-pass element in precision regulators.

schematic



Resistor values shown are nominal.

absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Input voltage, V _I		. 35 V
Operating virtual junction temperature, T _J		150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds		260°C
Storage temperature range, T _{stg} 6	35°C to	150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

package thermal data (see Note 1)

PACKAGE	BOARD	θЈС	θ JA
POWER-FLEX (KTP)	High K, JESD 51-5	19°C/W	28°C/W
SOT-223 (DCY)	High K, JESD 51-7	4°C/W	53°C/W
TO-220 (KC/KCS)	High K, JESD 51-5	3°C/W	19°C/W

NOTE 1: Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

recommended operating conditions

			MIN	MAX	UNIT
		μΑ78Μ33	5.3	25	
		μΑ78Μ05	7	25	
		μΑ78Μ06	8	25	
M. Input valtage	lanutualtara	μΑ78Μ08	10.5	25	V
VI	nput voltage μΑ78M09	11.5	26	V	
		μΑ78Μ10	12.5	28	
		μA78M12	14.5	30	
		μΑ78Μ15	17.5	4.5 30	
IO Output current				500	mA
TJ	T _J Operating virtual junction temperature		0	125	°C

electrical characteristics at specified virtual junction temperature, V_I = 8 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER		a constraint	μ Α	78M330	;	UNIT	
PARAMETER	TES	ST CONDITIONS†	MIN	TYP	MAX		
Output and to made	$I_{O} = 5 \text{ mA to } 350 \text{ mA},$		3.2	3.3	3.4	V	
Output voltage‡	V _I = 8 V to 20 V	$T_J = 0$ °C to 125°C	3.1	3.3	3.5		
Input voltage regulation	lo - 200 mA	V _I = 5.3 V to 25 V		9	100	mV	
Input voltage regulation	I _O = 200 mA	V _I = 8 V to 25 V		3	50	IIIV	
Dinnie rejection	V _I = 8 V to 18 V,	$I_O = 100 \text{ mA}, T_J = 0^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	62			dB	
Ripple rejection	f = 120 Hz	I _O = 300 mA	62	80		ub	
Output voltage regulation	V _I = 8 V,	I _O = 5 mA to 500 mA		20	100	mV	
Temperature coefficient of output voltage	$I_O = 5 \text{ mA},$	$T_J = 0$ °C to 125°C		-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz			40	200	μV	
Dropout voltage				2		V	
Bias current				4.5	6	mA	
Dies surrent shangs	I _O = 200 mA,	V _I = 8 V to 25 V, T _J = 0°C to 125°C			0.8	А	
Bias current change	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$				0.5	mA	
Short-circuit output current	V _I = 35 V			300		mA	
Peak output current				700		mA	

[†] All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, $V_I = 10 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER		a constraint	μ Α78M05C		;	UNIT	
PARAWETER	IES	ST CONDITIONS†	MIN TYP MAX			0.411	
Output and to me	$I_{O} = 5 \text{ mA to } 350 \text{ mA},$		4.8	5	5.2	V	
Output voltage	$V_{I} = 7 V \text{ to } 20 V$	T _J = 0°C to 125°C	4.75		5.25	V	
Input voltage regulation	I _O = 200 mA	V _I = 7 V to 25 V		3	100	mV	
Input voltage regulation	I() = 200 IIIA	V _I = 8 V to 25 V		1	50	IIIV	
Ripple rejection	$V_{I} = 8 \text{ V to } 18 \text{ V},$	$I_{O} = 100 \text{ mA}, T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	62			dB	
	f = 120 Hz	I _O = 300 mA	62	80		aв	
Output voltage regulation	$I_O = 5 \text{ mA to } 500 \text{ mA}$			20	100	mV	
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$			10	50	111 V	
Temperature coefficient of output voltage	$I_O = 5 \text{ mA},$	$T_J = 0$ °C to 125°C		-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz			40	200	μV	
Dropout voltage				2		V	
Bias current				4.5	6	mA	
Dies surrent change	$I_O = 200 \text{ mA},$	$V_I = 8 \text{ V to } 25 \text{ V}, T_J = 0^{\circ}\text{C to } 125^{\circ}\text{C}$			0.8	mA	
Bias current change	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$				0.5	IIIA	
Short-circuit output current	V _I = 35 V			300		mA	
Peak output current				0.7		Α	

[†] All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, V_I = 11 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER				μ Α78Μ06C		UNIT	
PARAMETER		TEST CONDITIONS†		MIN	TYP	MAX	UNII
Outrout walks as	I _O = 5 mA to 350 mA,	V _I = 8 V to 21 V		5.75	6	6.25	V
Output voltage	10 = 3 mA to 330 mA,	V = 0 V 10 21 V	$T_J = 0$ °C to 125°C	5.7		6.3	V
Input voltage regulation	lo - 200 mA	V _I = 8 V to 25 V			5	100	mV
	I _O = 200 mA	V _I = 9 V to 25 V			1.5	50	IIIV
Ripple rejection	V _I = 9 V to 19 V,	f = 120 Hz	$I_O = 100 \text{ mA},$ $T_J = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	59			dB
			I _O = 300 mA	59	80		
Output voltage regulation	$I_O = 5 \text{ mA to } 500 \text{ mA}$				20	120	mV
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	60	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	T _J = 0°C to 125°C			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				45		μV
Dropout voltage					2		V
Bias current					4.5	6	mA
Dice current change	V _I = 9 V to 25 V,	I _O = 200 mA,	T _J = 0°C to 125°C			0.8	A
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	mA
Short-circuit output current	V _I = 35 V				270		mA
Peak output current		_			0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER				μ Α78M08C			UNIT	
PARAMETER		TEST CONDITIONS†		MIN	ONIT			
Output wells we	V _I = 10.5 V to 23 V,	I _O = 5 mA to 350 mA		7.7	8	8.3	V	
Output voltage	V = 10.5 V to 25 V,	10 = 3 IIIA to 330 IIIA	$T_J = 0$ °C to 125°C	7.6		8.4	V	
Input voltage regulation	In - 200 mA	V _I = 10.5 V to 25 V			6	100	mV	
input voltage regulation	I _O = 200 mA	V _I = 11 V to 25 V			2	50	IIIV	
Pinnle rejection	V _I = 11.5 V to 21.5 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	56			dB	
Ripple rejection	f = 120 Hz	I _O = 300 mA		56	80		uБ	
Output voltage regulation	I _O = 5 mA to 500 mA				25	160	o mV	
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	80	IIIV	
Temperature coefficient of output voltage	I _O = 5 mA,	$T_J = 0$ °C to 125°C			-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz				52		μV	
Dropout voltage					2		V	
Bias current					4.6	6	mA	
Diag assument about	V _I = 10.5 V to 25 V,	I _O = 200 mA,	T _J = 0°C to 125°C			0.8	A	
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	mA	
Short-circuit output current	V _I = 35 V				250		mA	
Peak output current					0.7		Α	

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



electrical characteristics at specified virtual junction temperature, $V_I = 16 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER				μ Α78Μ09C			UNIT	
PARAMETER		TEST CONDITIONS†		MIN	TYP	MAX	UNIT	
Outrottualiana	V _I = 11.5 V to 24 V,	lo = 5 m/ to 350 m/		8.6	9	9.4	V	
Output voltage	V = 11.5 V to 24 V,	$I_O = 5 \text{ mA to } 350 \text{ mA}$	$T_J = 0^{\circ}C$ to $125^{\circ}C$	8.5		9.5	V	
Input voltage regulation	IO = 200 mA	V _I = 11.5 V to 26 V			6	100	mV	
	10 = 200 IIIA	V _I = 12 V to 26 V			2	50	IIIV	
Pinnle rejection	V _I = 13 V to 23 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	56			dB	
Ripple rejection	f = 120 Hz	I _O = 300 mA		56	80		uБ	
Output wells as a souletter	$I_O = 5 \text{ mA to } 500 \text{ mA}$				25	180) mV	
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	90	IIIV	
Temperature coefficient of output voltage	I _O = 5 mA,	T _J = 0°C to 125°C			-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz				58		μV	
Dropout voltage					2		V	
Bias current					4.6	6	mA	
Dice current change	V _I = 11.5 V to 26 V,	I _O = 200 mA,	$T_J = 0^{\circ}C$ to $125^{\circ}C$			0.8	A	
Bias current change	$I_O = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	mA	
Short-circuit output current	V _I = 35 V				250		mA	
Peak output current					0.7		Α	

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 17 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

DADAMETED				μ Α78M10C			UNIT	
PARAMETER		TEST CONDITIONS†		MIN	UNIT			
O to to allow	V _I = 12.5 V to 25 V,	la - 5 m \ to 350 m \		9.6	10	10.4	V	
Output voltage	V = 12.5 V to 25 V,	$I_O = 5 \text{ mA to } 350 \text{ mA}$	$T_J = 0$ °C to 125°C	9.5		10.5	V	
Innut valtage regulation	IO = 200 mA	V _I = 12.5 V to 28 V	/ /		7	100	mV	
Input voltage regulation	IO = 200 IIIA	V _I = 14 V to 28 V			2	50	IIIV	
Dipple rejection	V _I = 15 V to 25 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	59			dB	
Ripple rejection	f = 120 Hz	I _O = 300 mA		55	80		uБ	
0	$I_O = 5 \text{ mA to } 500 \text{ mA}$			25 200		mV		
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	100	IIIV	
Temperature coefficient of output voltage	I _O = 5 mA,	$T_J = 0$ °C to 125°C			-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz				64		μV	
Dropout voltage		(4)			2		V	
Bias current					4.7	6	mA	
Dies surrent change	V _I = 12.5 V to 28 V,	I _O = 200 mA,	T _J = 0°C to 125°C			0.8	A	
Bias current change	$I_O = 5$ mA to 350 mA,	T _J = 0°C to 125°C				0.5	mA	
Short-circuit output current	V _I = 35 V				245		mA	
Peak output current					0.7		Α	

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



electrical characteristics at specified virtual junction temperature, $V_I = 19 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER		TEST SOMETIONS!		μ Α78M12C MIN TYP MAX			UNIT	
PARAMETER		TEST CONDITIONS†					UNIT	
Outrost walks as	V _I = 14.5 V to 27 V,	I _O = 5 mA to 350 mA		11.5	12	12.5	V	
Output voltage	V = 14.5 V to 27 V,	1Q = 2 IIIY 10 220 IIIY	$T_J = 0$ °C to 125°C	11.4		12.6	V	
Input voltage regulation	IO = 200 mA	V _I = 14.5 V to 30 V			8	100	mV	
	IO = 200 IIIA	V _I = 16 V to 30 V			2	50	IIIV	
Ripple rejection	V _I = 15 V to 25 V,	I _O = 100 mA,	$T_J = 0$ °C to 125°C	55			dB	
	f = 120 Hz	I _O = 300 mA		55	80		uБ	
Output voltage regulation	$I_O = 5 \text{ mA to } 500 \text{ mA}$				25	240	mV	
Output voltage regulation	$I_O = 5 \text{ mA to } 200 \text{ mA}$				10	120	IIIV	
Temperature coefficient of output voltage	I _O = 5 mA				-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz				75		μV	
Dropout voltage					2		V	
Bias current					4.8	6	mA	
Ding gurrant shangs	V _I = 14.5 V to 30 V,	I _O = 200 mA,	T _J = 0°C to 125°C			0.8	A	
Bias current change	$I_0 = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	mA	
Short-circuit output current	V _I = 35 V				240		mA	
Peak output current					0.7		Α	

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, $V_I = 23 \text{ V}$, $I_O = 350 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

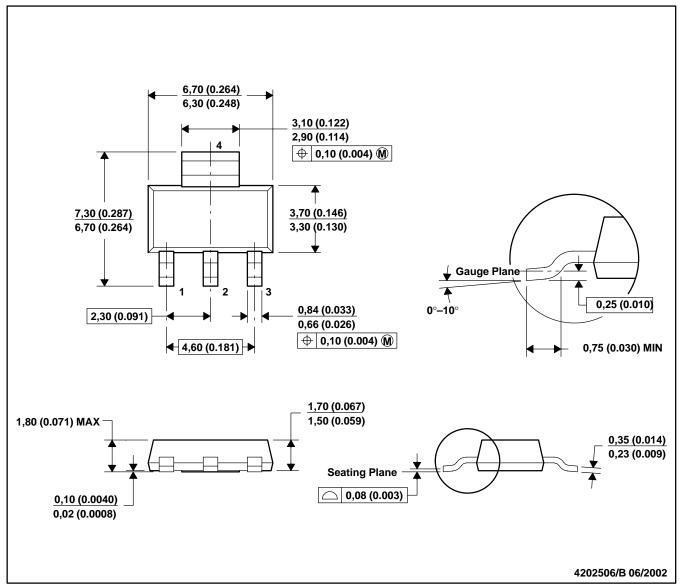
DADAMETED				μ Α	μ Α78M15C		
PARAMETER		TEST CONDITIONS†				MAX	UNIT
Outroductions	\/\. = 17.5 \/ to 20 \/	lo - 5 m/ to 250 m/		14.4	15	15.6	\/
Output voltage	$V_{I} = 17.5 \text{ V to } 30 \text{ V},$	$I_O = 5 \text{ mA to } 350 \text{ mA}$	T _J = 0°C to 125°C	14.25		15.75	1
Input voltage regulation	lo - 200 mA	V _I = 17.5 V to 30 V			10	100	m\/
	I _O = 200 mA	V _I = 20 V to 30 V			3	50	m∨
	$V_{I} = 18.5 \text{ V to } 28.5 \text{ V},$	I _O = 100 mA,	$T_J = 0$ °C to 125°C	54			dB
	f = 120 Hz	I _O = 300 mA		54	70		uБ
Output wells as as addition	I _O = 5 mA to 500 mA	I _O = 5 mA to 500 mA			25	300	mV
Output voltage regulation	I _O = 5 mA to 200 mA				10	150	IIIV
Temperature coefficient of output voltage	I _O = 5 mA,	$T_J = 0$ °C to 125°C			-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				90		μV
Dropout voltage		4/2			2		V
Bias current					4.8	6	mA
Diag gurrant shangs	V _I = 17.5 V to 30 V,	$I_{O} = 200 \text{ mA},$	$T_J = 0^{\circ}C$ to $125^{\circ}C$			0.8	mA
Bias current change	$I_0 = 5 \text{ mA to } 350 \text{ mA},$	T _J = 0°C to 125°C				0.5	IIIA
Short-circuit output current	V _I = 35 V				240		mA
Peak output current					0.7		Α

[†] All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.



DCY (R-PDSO-G4)

PLASTIC SMALL-OUTLINE



NOTES: A. All linear dimensions are in millimeters (inches).

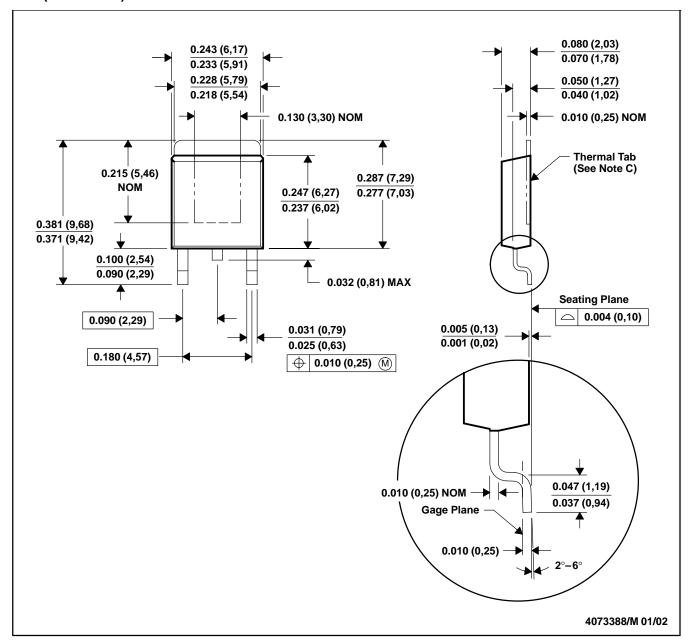
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion.

D. Falls within JEDEC TO-261 Variation AA.

KTP (R-PSFM-G2)

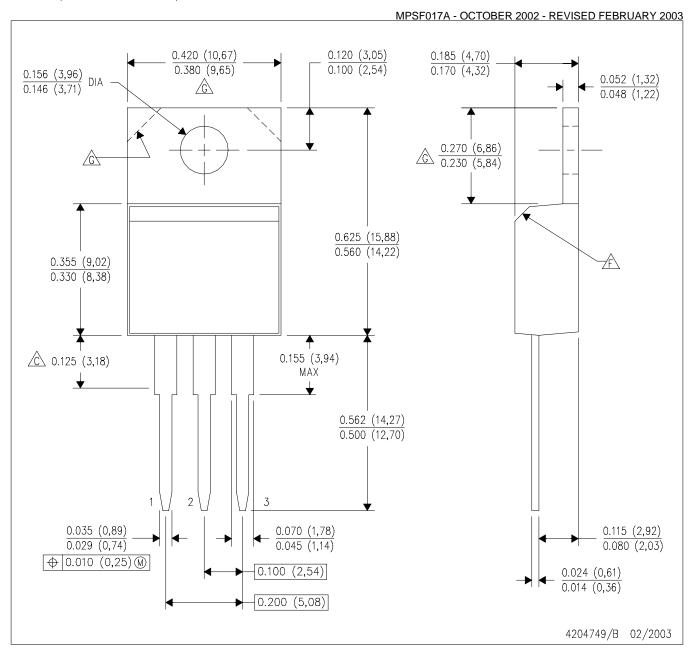
PowerFLEX™ PLASTIC FLANGE-MOUNT PACKAGE



- NOTES: A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. The center lead is in electrical contact with the thermal tab.
 - D. Dimensions do not include mold protrusions, not to exceed 0.006 (0,15).
 - E. Falls within JEDEC TO-252 variation AC.

PowerFLEX is a trademark of Texas Instruments.





NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.

Lead dimensions are not controlled within this area.

- D. All lead dimensions apply before solder dip.
- E. The center lead is in electrical contact with the mounting tab.

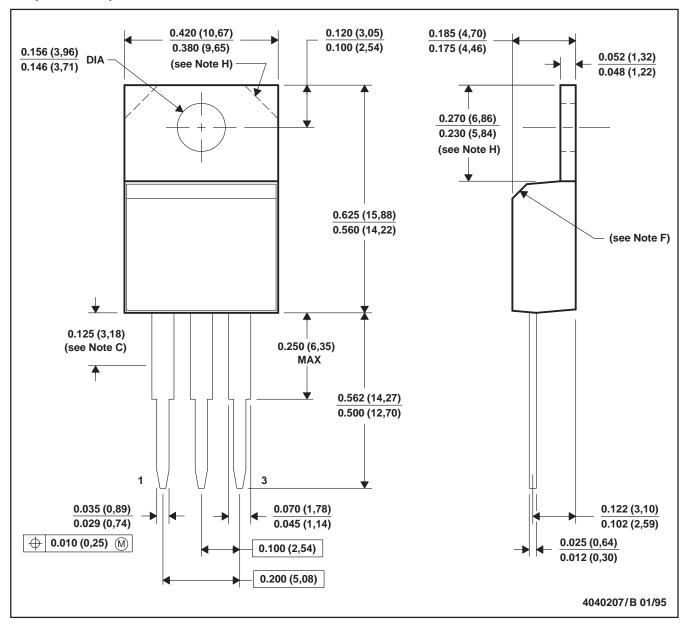
The chamfer is optional.

Tab contour optional within these dimensions.

H. Falls within JEDEC TO-220 variation AB.

KC (R-PSFM-T3)

PLASTIC FLANGE-MOUNT PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Lead dimensions are not controlled within this area.
- D. All lead dimensions apply before solder dip.
- E. The center lead is in electrical contact with the mounting tab.
- F. The chamfer is optional.
- G. Falls within JEDEC TO-220AB
- H. Tab contour optional within these dimensions



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